PRELIMINARY

CY7C1011

128K x 16 Static RAM

Features

- **High speed**
  - **— t_{AA} = 15 ns**
- **Low active power**
  - **— 1150 mW (max.)**
- **Low CMOS standby power (L version)**
  - **— 40 mW (max.)**
- **2.0V Data Retention (4 mW at 2.0V retention)**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**

Functional Description

The CY7C1011 is a high-performance CMOS static RAM organized as 131,072 words by 16 bits.

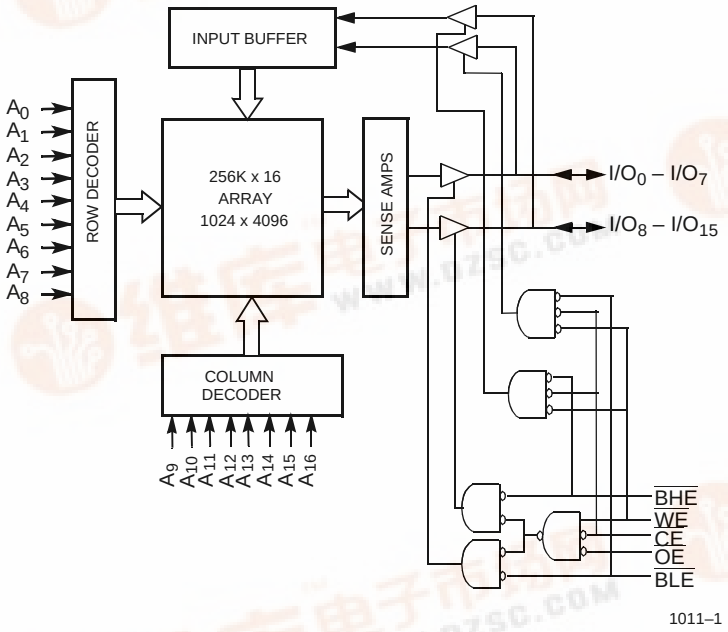
Writing to the device is accomplished by taking chip enable ($\overline{CE}$) and write enable ($\overline{WE}$) inputs LOW. If byte low enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{16}). If byte high enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking chip enable ($\overline{CE}$) and output enable ($\overline{OE}$) LOW while forcing the write enable ($\overline{WE}$) HIGH. If byte low enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If byte high enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this datasheet for a complete description of read and write modes.

The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), the $\overline{BHE}$ and $\overline{BLE}$ are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

The CY7C1011 is available in a standard 44-pin TSOP II package with center power and ground (revolutionary) pinout.

Logic Block Diagram



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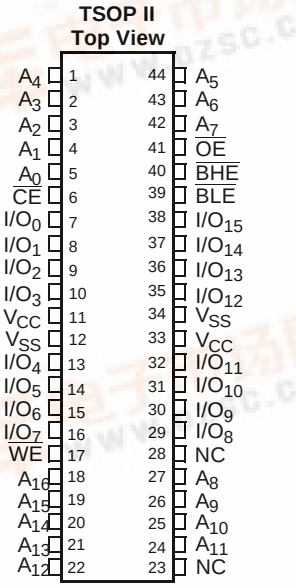
Pin Configuration



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Selection Guide

		7C1011-15	7C1011-20	7C1011-25
Maximum Access Time (ns)		15	20	25
Maximum Operating Current (mA)		230	220	200
Maximum CMOS Standby Current (mA)	Com'l	8	8	8

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[1] .... –0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State[1] ..... –0.5V to V_{CC} + 0.5V

DC Input Voltage[1] ..... –0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Operating Range

Range	Ambient Temperature[2]	V_{CC}
Commercial	0°C to +70°C	5V ± 0.5

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		7C1011-15		7C1011-20		7C1011-25		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage[1]			–0.5	0.8	–0.5	0.8	–0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		–1	+1	–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled		–1	+1	–1	+1	–1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = 1/t_{RC}			230		220		200	mA
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}			40		40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f=0	Com'l		8		8		8	mA

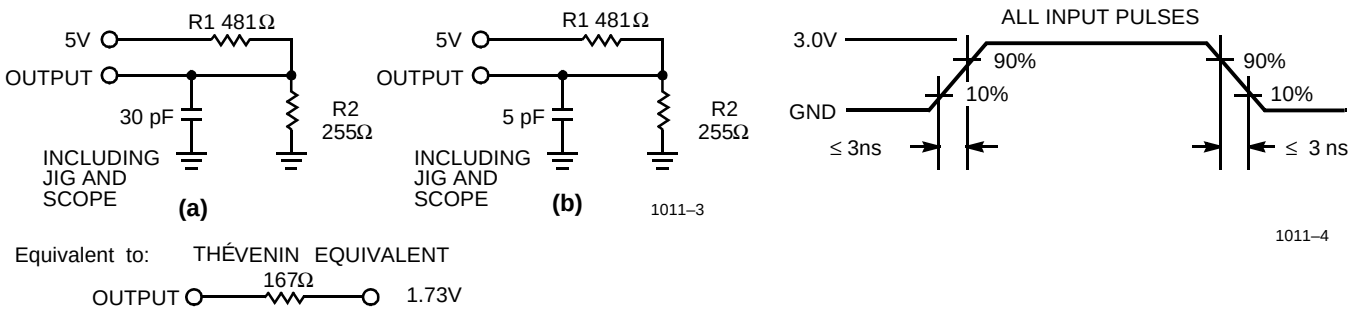
Capacitance[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	8	pF
C_{OUT}	I/O Capacitance		8	pF

Notes:

1. V_{IL} (min.) = –2.0V for pulse durations of less than 20 ns.
2. T_A is the "instant on" case temperature.
3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Switching Characteristics[4] Over the Operating Range

Parameter	Description	7C1011-15		7C1011-20		7C1011-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
t_{RC}	Read Cycle Time	15		20		25		ns
t_{AA}	Address to Data Valid		15		20		25	ns
t_{OHA}	Data Hold from Address Change	3		3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		15		20		25	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		7		8		10	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[5]	0		0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[5, 6]		7		8		10	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[5]	3		3		5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[5, 6]		7		8		10	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		15		20		25	ns
t_{DBE}	Byte Enable to Data Valid		7		8		10	ns
t_{LZBE}	Byte Enable to Low Z	0		0		0		ns
t_{HZBE}	Byte Disable to High Z		7		8		10	ns
WRITE CYCLE[7,8]								
t_{WC}	Write Cycle Time	15		20		25		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	12		13		15		ns
t_{AW}	Address Set-Up to Write End	12		13		15		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	12		13		15		ns
t_{SD}	Data Set-Up to Write End	8		9		10		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[5]	3		3		5		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[5, 6]		7		8		10	ns
t_{BW}	Byte Enable to End of Write	12		13		15		ns

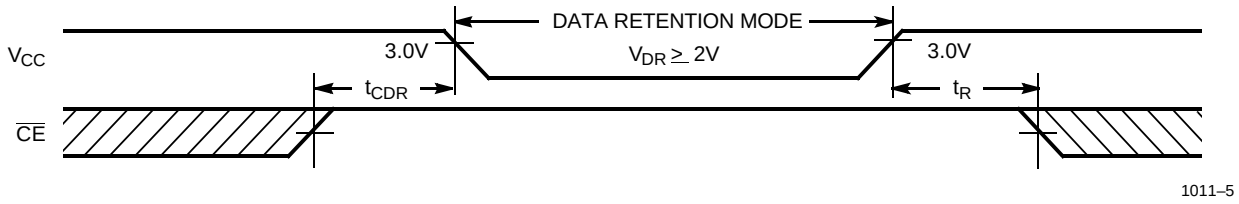
Notes:

4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
5. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
6. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
7. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
8. The minimum write cycle time for Write Cycle no. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Data Retention Characteristics Over the Operating Range

Parameter	Description		Conditions[10]	Min.	Max.	Unit
V_{DR}	V_{CC} for Data Retention			2.0		V
I_{CCDR}	Data Retention Current	Com'l	$V_{CC} = V_{DR} = 2.0V$, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		2	mA
t_{CDR}[3]	Chip Deselect to Data Retention Time			0		ns
t_R[9]	Operation Recovery Time			t_{RC}		ns

Data Retention Waveform



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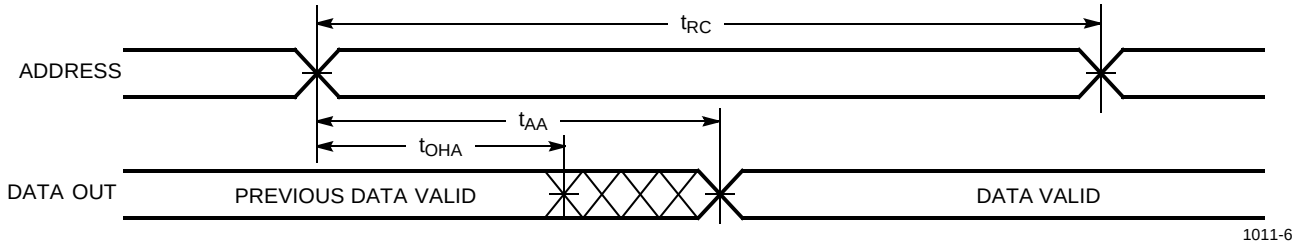
Switching Waveforms

Read Cycle No. 1 [11, 12]



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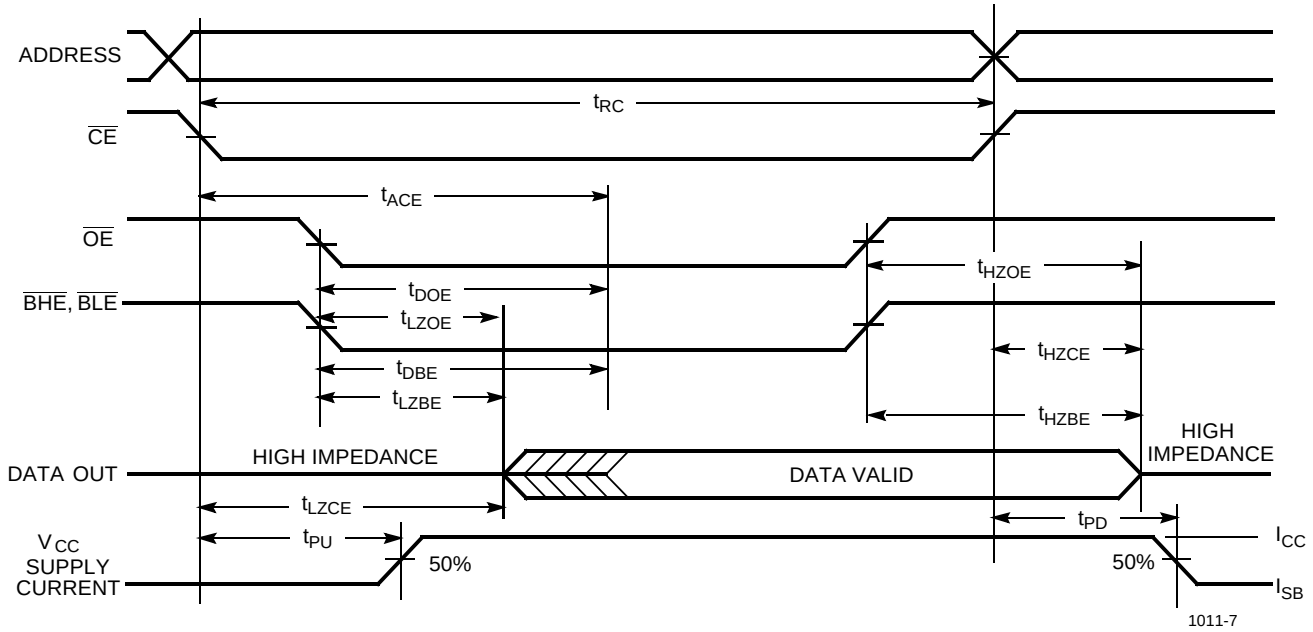
Notes:

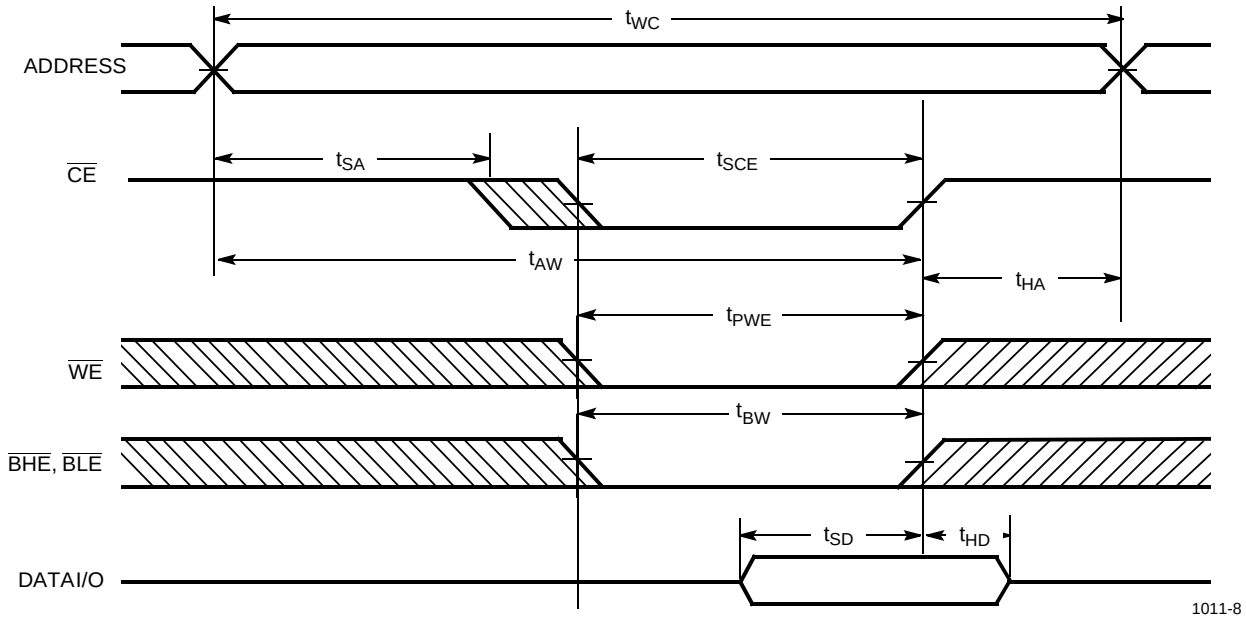
9. $t_r \leq 3$ ns for the –12 and –15 speeds. $t_r \leq 5$ ns for the –20 and slower speeds.
10. No input may exceed V_{CC} + 0.5V.
11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$, and/or $\overline{BHE} = V_{IL}$.
12. $\overline{WE}$ is HIGH for read cycle.

Switching Waveforms (continued)

Read Cycle No. 2 ($\overline{OE}$ Controlled) [12, 13]



Write Cycle No. 1 ($\overline{CE}$ Controlled) [14, 15]

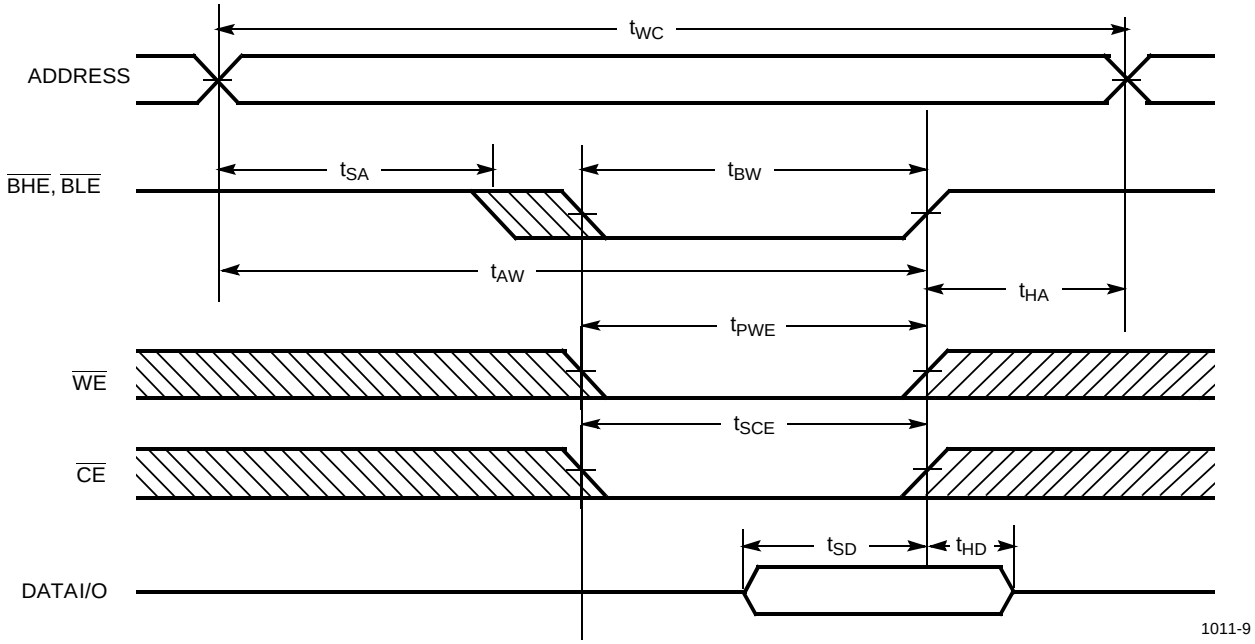


Notes:

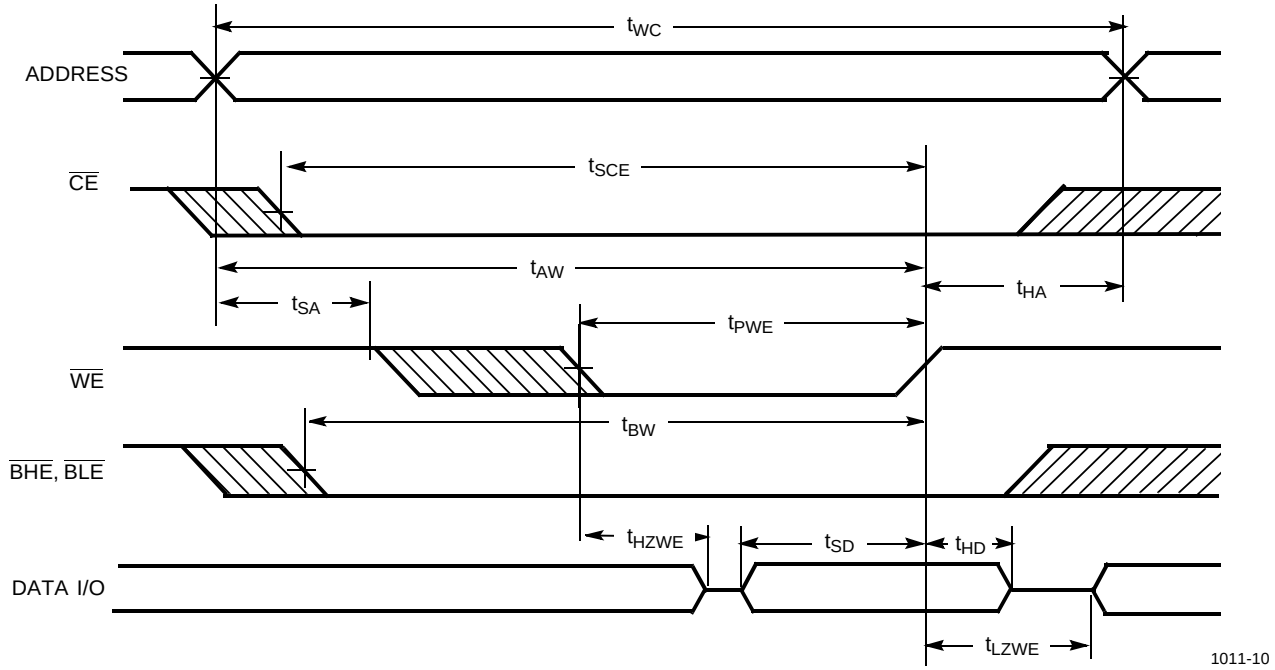
13. Address valid prior to or coincident with $\overline{CE}$ transition LOW.
14. Data I/O is high impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$= V_{IH}.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)



Truth Table

CE	OE	WE	BLE	BHE	I/O_0–I/O_7	I/O_8–I/O_{15}	Mode	Power
H	X	X	X	X	High Z	High Z	Power Down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read All bits	Active (I_{CC})
L	L	H	L	H	Data Out	High Z	Read Lower bits only	Active (I_{CC})
L	L	H	H	L	High Z	Data Out	Read Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write All bits	Active (I_{CC})
L	X	L	L	H	Data In	High Z	Write Lower bits only	Active (I_{CC})
L	X	L	H	L	High Z	Data In	Write Upper bits only	Active (I_{CC})
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1011-15VC	Z44	44-Lead TSOP Type II	Commercial
20	CY7C1011-20VC	Z44	44-Lead TSOP Type II	
25	CY7C1011-25ZC	Z44	44-Lead TSOP Type II	

Document #: 38-00744

Package Diagram

44-Pin TSOP II Z44